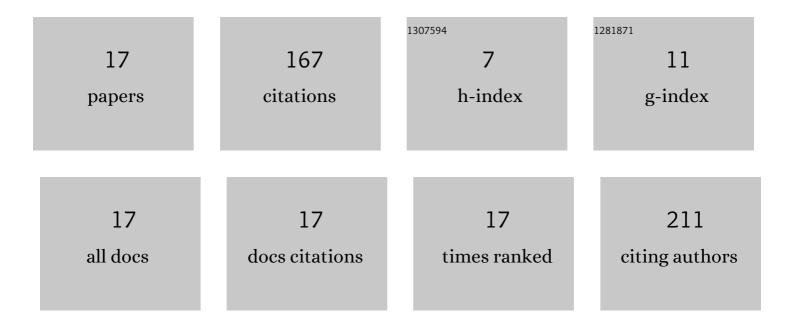
Dmytro V Korbutyak

List of Publications by Year in descending order

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DMVTDO V KODBUTVAK

#	Article	IF	CITATIONS
1	Thin polymer films with embedded CdS nanocrystals. Colloid and Polymer Science, 2015, 293, 1159-1169.	2.1	6
2	Nonresonant Surface-Enhanced Raman Scattering of ZnO Quantum Dots with Au and Ag Nanoparticles. ACS Nano, 2013, 7, 3420-3426.	14.6	74
3	Electrical properties and low-temperature photolumincesence of Si-doped CdTe crystals. Semiconductors, 2006, 40, 143-147.	0.5	7
4	Influence of layer deformation on thermal quenching of exciton photoluminescence in short-period GaAs/AlAs superlattices. Semiconductor Science and Technology, 2004, 19, 475-479.	2.0	7
5	Gamma-radiation effect on donor and acceptor states in CdTe and CdTe:Cl. Journal of Alloys and Compounds, 2004, 371, 142-145.	5.5	9
6	Characterization of ultrashort-period GaAs/AlAs superlattices by exciton photoluminescence. Materials Science and Engineering C, 2002, 19, 439-443.	7.3	2
7	Observation of stimulated emission in an ultrashort-period nonsymmetric GaAs/AlAs superlattice. Applied Physics Letters, 2001, 78, 4085-4087.	3.3	10
8	<title>Asymmetric short-period GaAs/AlAs superlattices for light-emitting devices</title> . , 2001, 4318, 263.		0
9	Time-resolved spectra and kinetics of the exciton photoluminescence in different types of GaAs/AlAs superlattices. Superlattices and Microstructures, 2001, 29, 57-66.	3.1	0
10	<title>Gamma-ray CdTe<Cl> and CdZnTe detectors: investigations and applications in radiation control devices</title> ., 2001, , .		0
11	Growth and characterization of high-resistivity CdTeã€^Cl〉. Journal of Crystal Growth, 1999, 197, 659-662.	1.5	15
12	Enhancement of the photoluminescence intensity in short-period GaAs/AlAs superlattices with different well and barrier thickness. Applied Physics Letters, 1999, 74, 2596-2598.	3.3	16
13	Chlorine-related photoluminescence of CdTe gamma detector material. , 1998, 3359, 293.		0
14	Electroluminescent control technique of dislocation density in GaP. , 1998, , .		0
15	Identification of electron-hole transitions in short-period GaAs/AlAs superlattices by time-resolved photoluminescence. , 1998, 3359, 182.		0
16	Enhancement of electron-phonon interaction in ultrashort-period GaAs/AlAs superlattices. Physical Review B, 1997, 55, 10621-10624.	3.2	15
17	Polarization effects in semiconductor superlattices. Semiconductor Science and Technology, 1995, 10, 422-424.	2.0	6